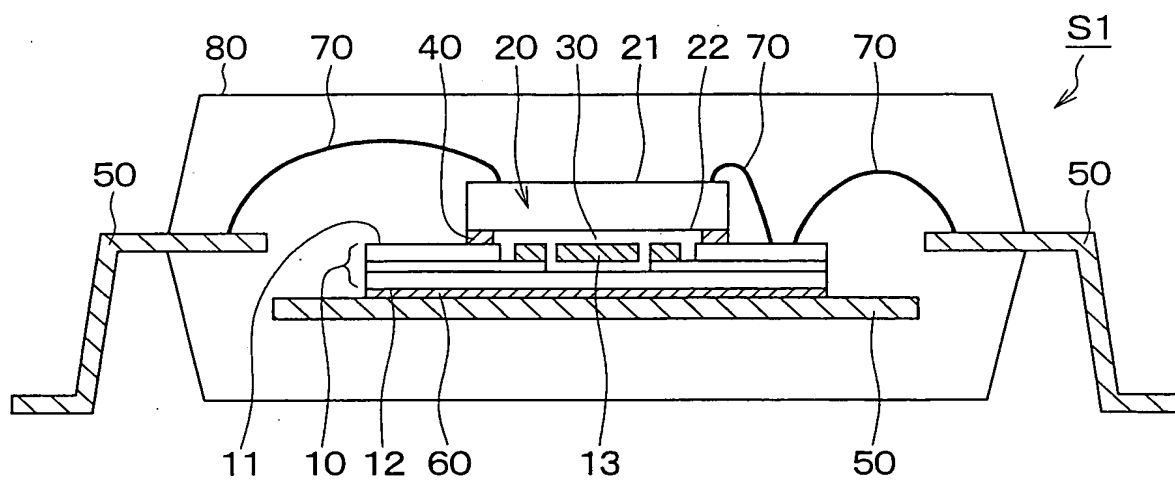
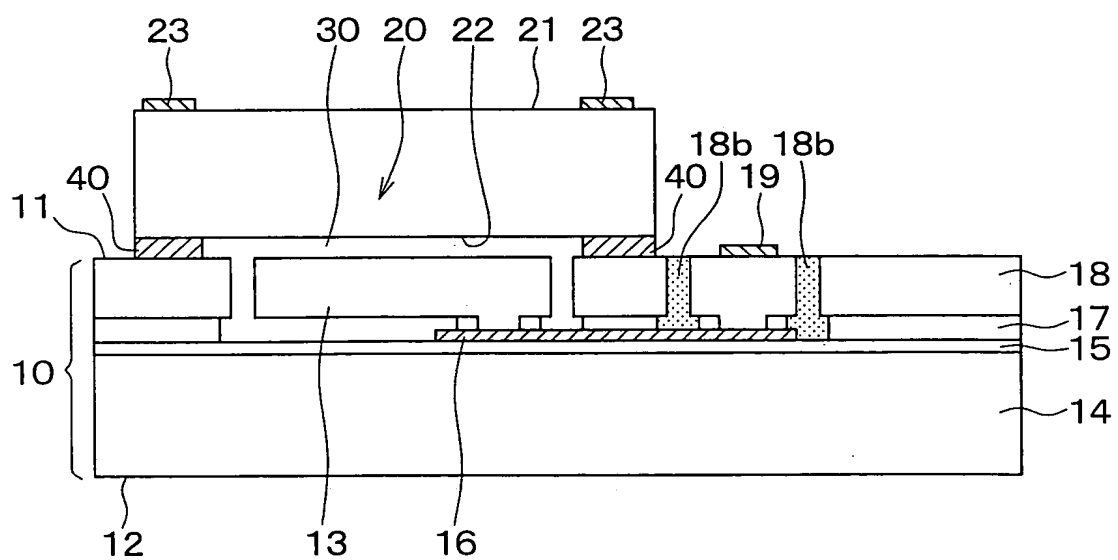


**FIG. 1**



**FIG. 3**



[illegible]

FIG. 4

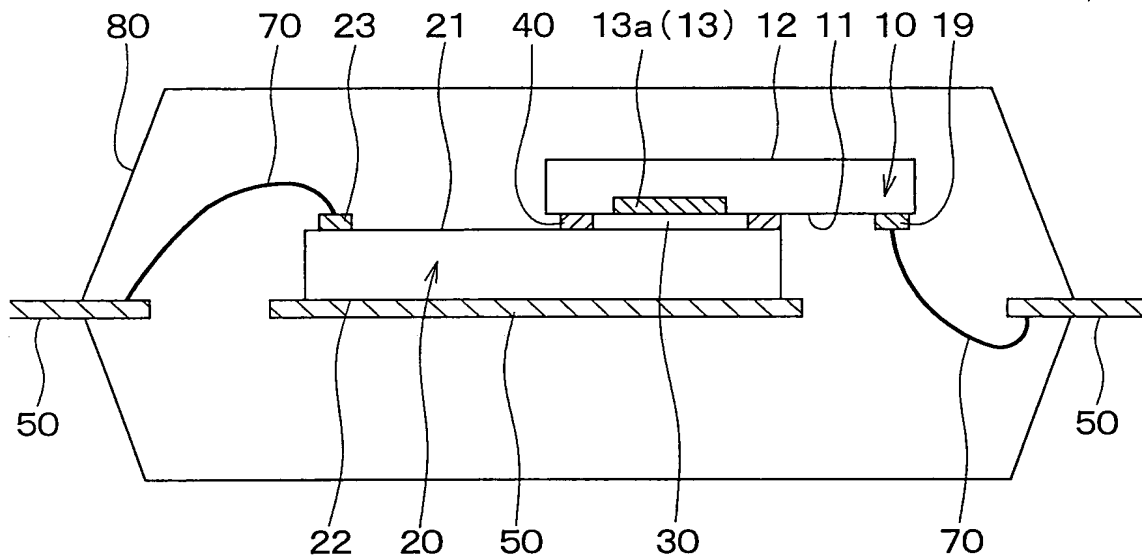


FIG. 5

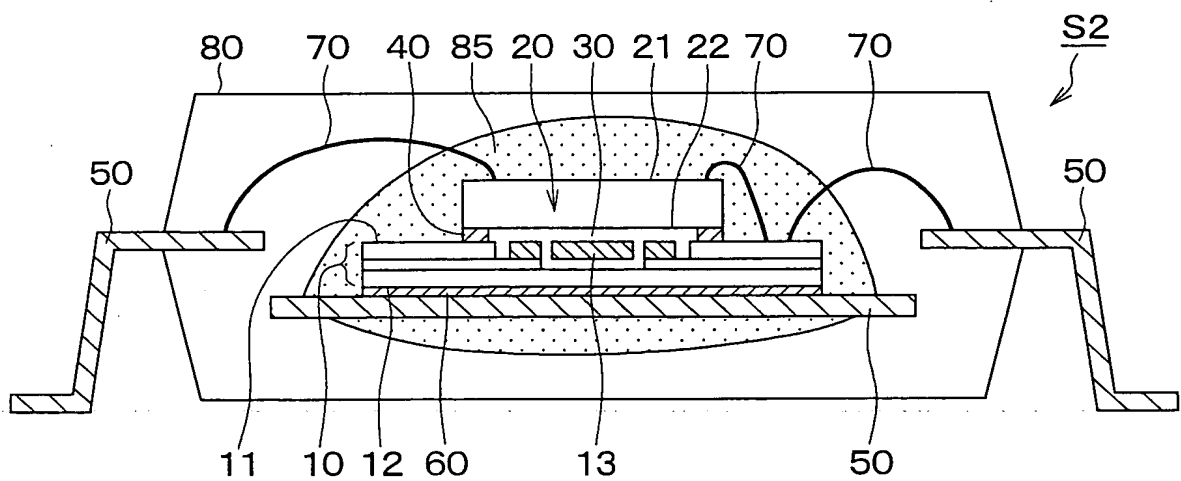


FIG. 6

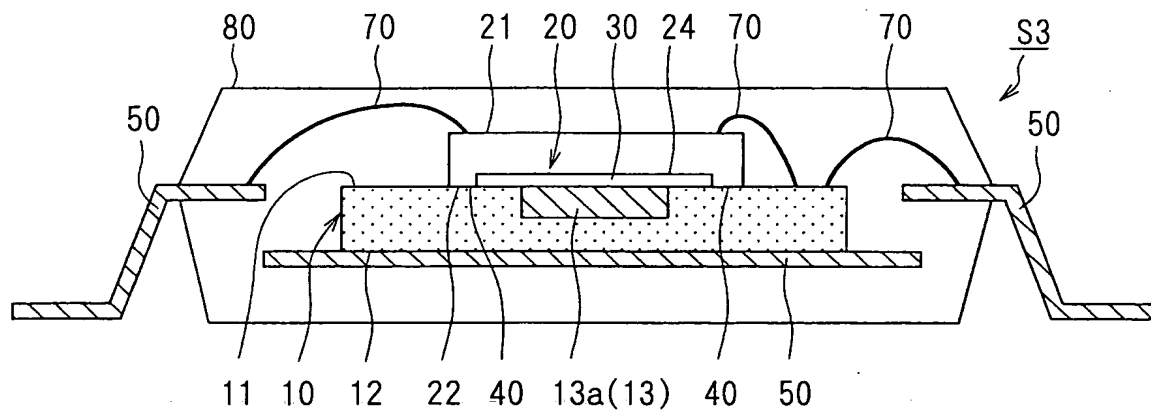


FIG. 7

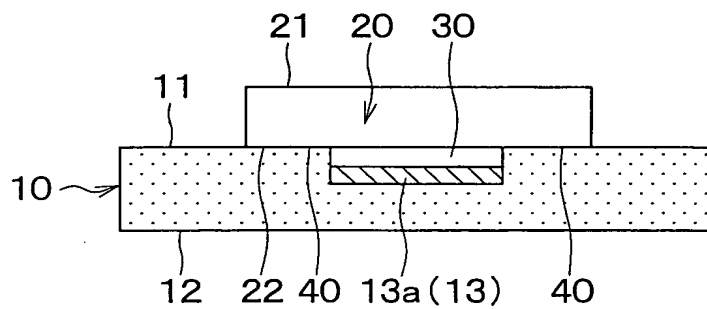
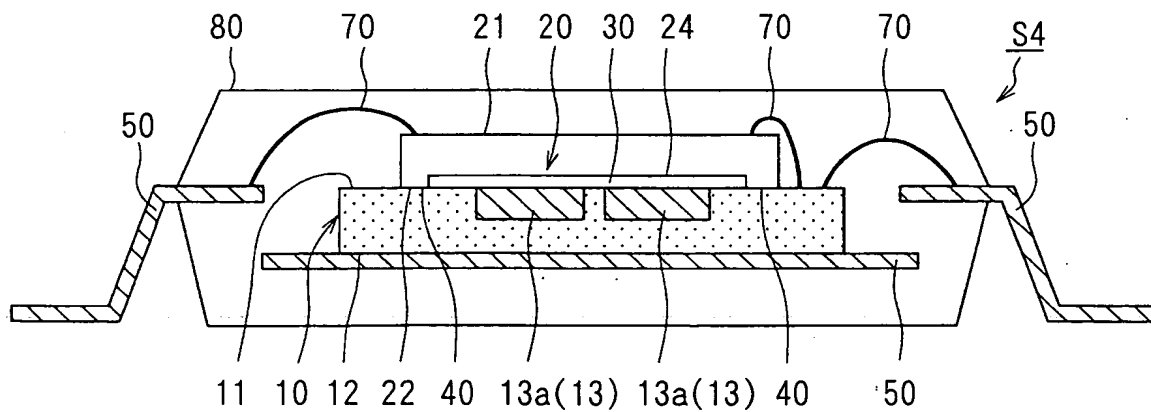
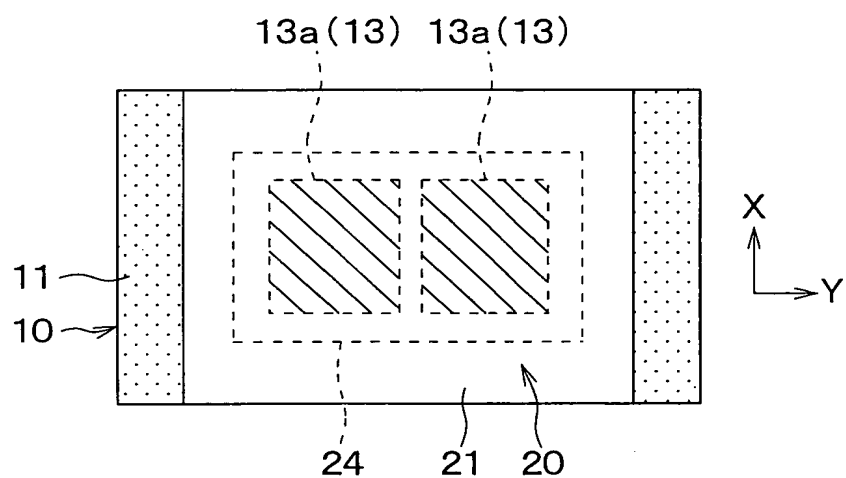


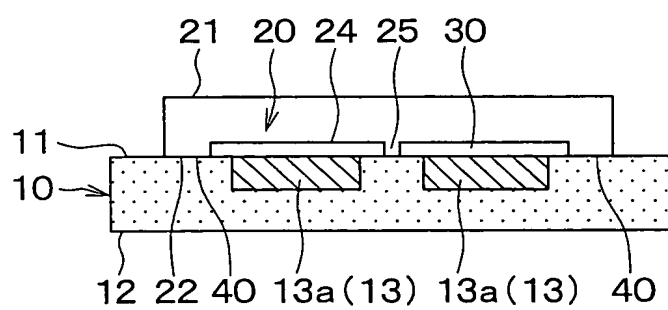
FIG. 8



**FIG. 9**



**FIG. 10**



[illegible]

A cross-sectional view of a semiconductor device. The diagram shows a substrate 80 with various layers and structures. A top layer 21 contains openings 20a and 20. Below this is a layer 11 with a central opening 40. Another layer 30 has a rectangular feature 24. A bottom layer 70 features two large circular openings or wells. A central region 10 is filled with a stippled pattern, representing a different material. This region is bounded by a hatched layer 12 and a lower hatched layer 13a(13). On the left and right sides, there are hatched regions labeled 50, which appear to be part of a larger structure 50. An arrow S6 points towards the right side of the device.

FIG. 12

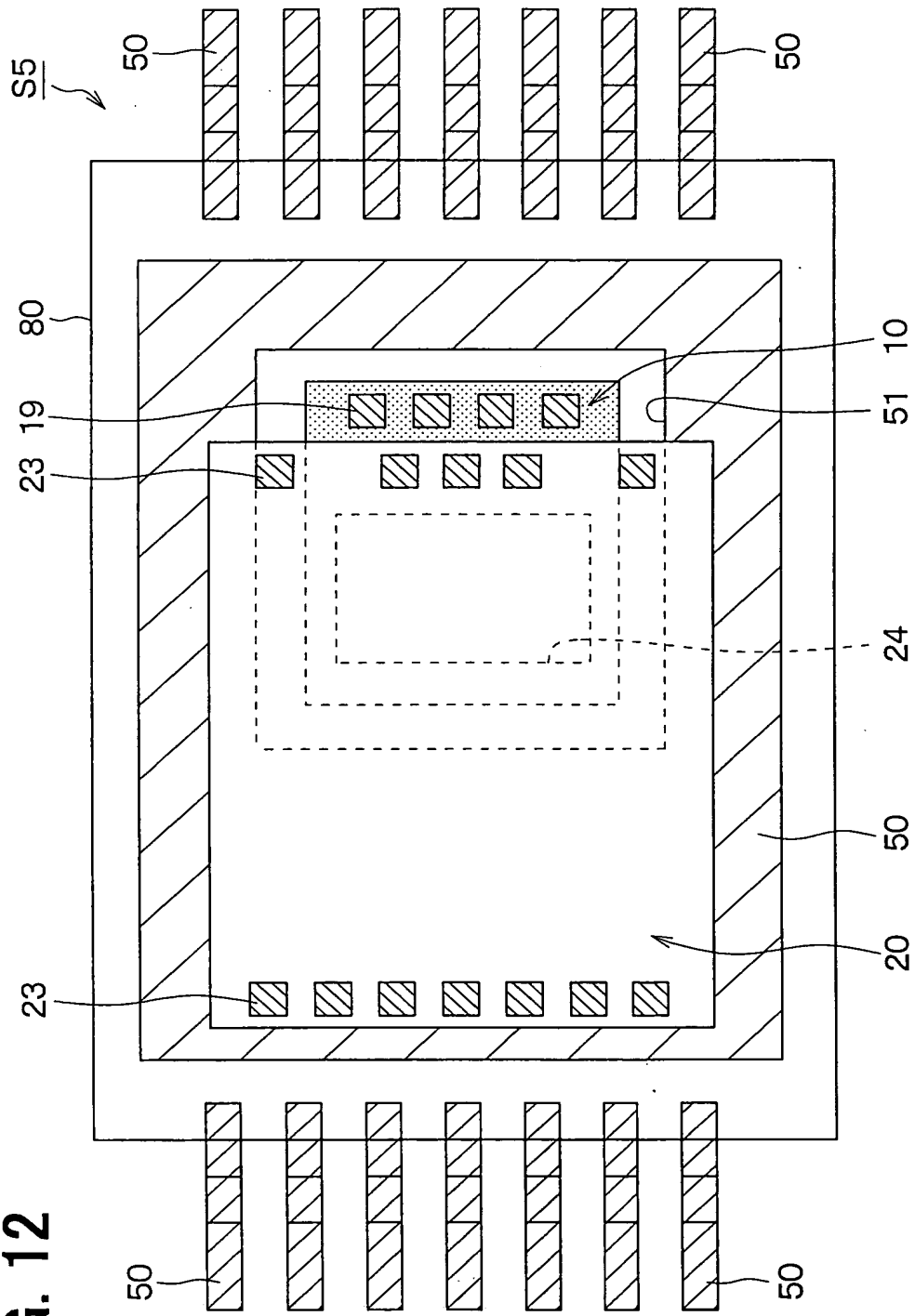


FIG. 14

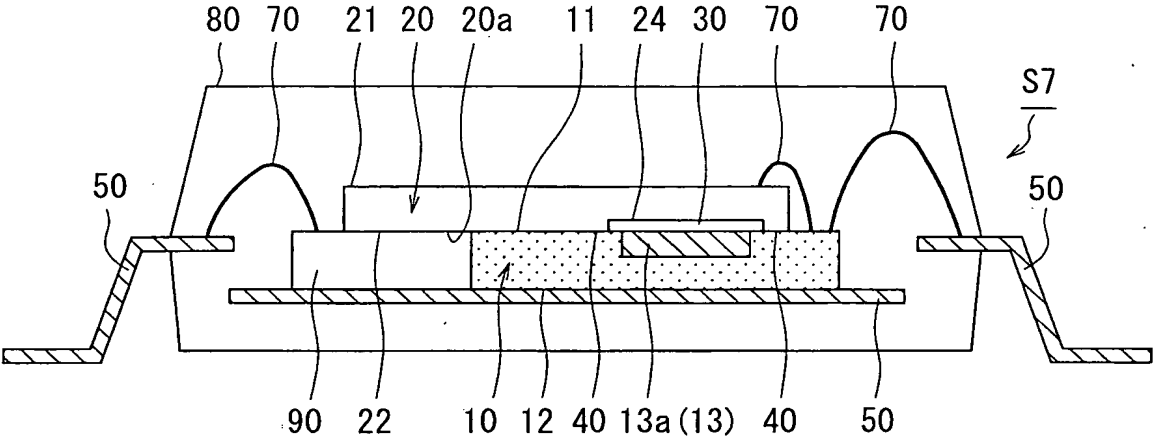


FIG. 15

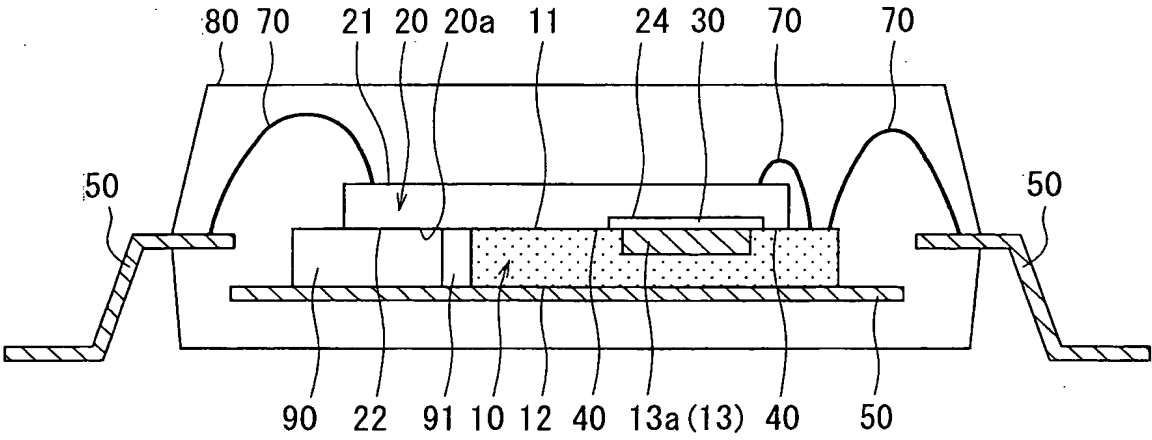
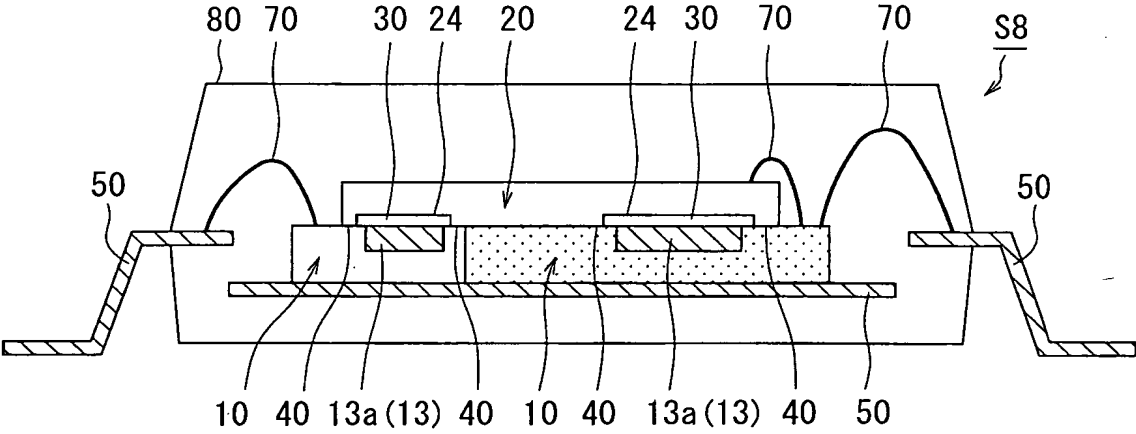
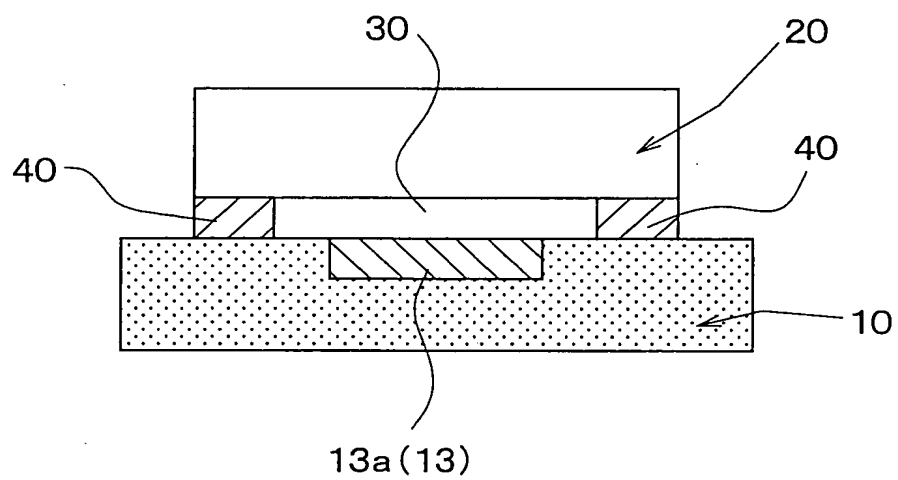




FIG. 16



**FIG. 17A**



**FIG. 17B**

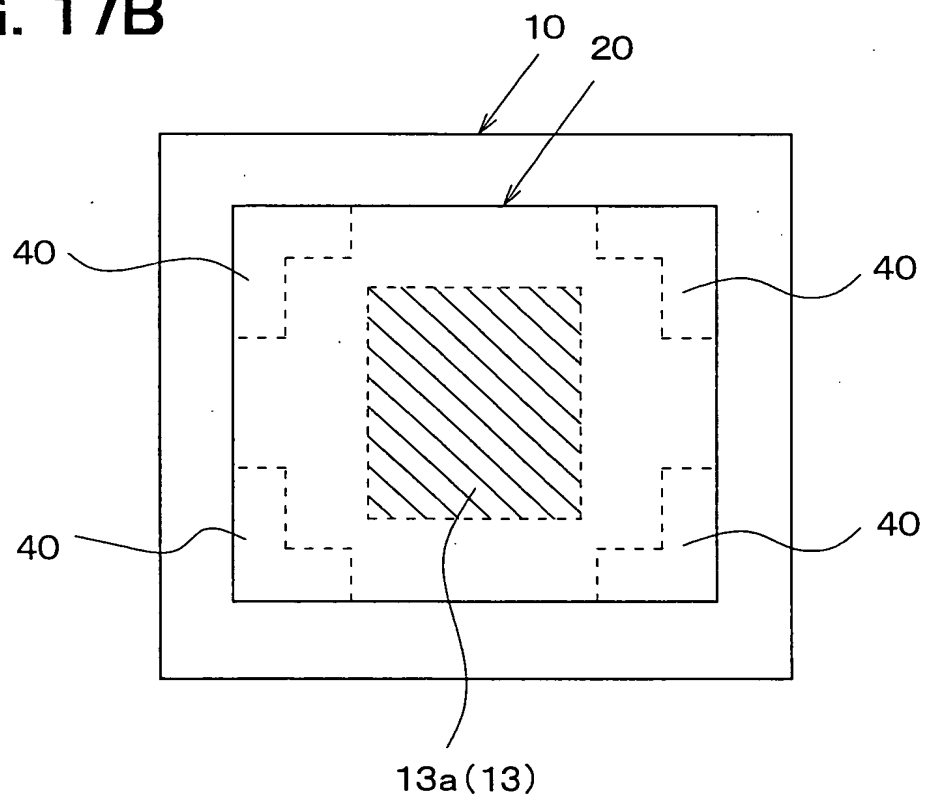
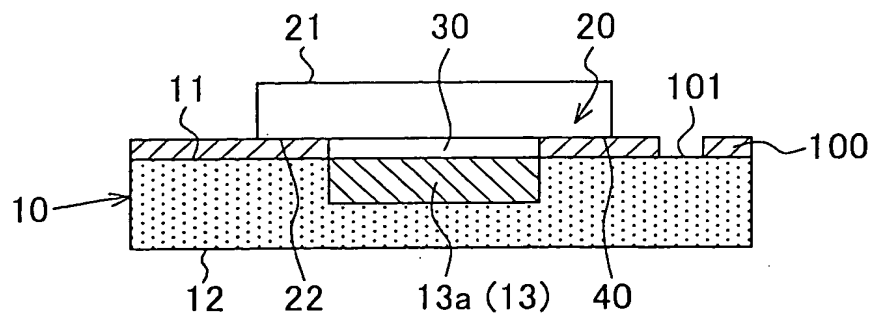


FIG. 18



**FIG. 19**  
**RELATED ART**

